

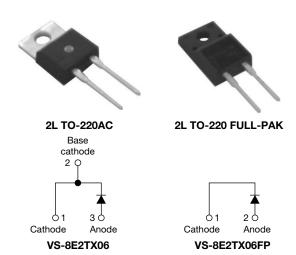
Vishay Semiconductors

RoHS

COMPLIANT

HALOGEN FREE

Hyperfast Rectifier, 8 A FRED Pt®



PRODUCT SUMMARY				
Package	2L TO-220AC, 2L TO-220 FP			
I _{F(AV)}	8 A			
V_{R}	600 V			
V _F at I _F	3.2 V			
t _{rr} (typ.)	13 ns			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Hyperfast recovery time, extremely low Q_{rr}
- 175 °C maximum operating junction temperature
- For PFC CCM operation
- True 2 pin package
- · Low forward voltage drop
- · Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- Compliant to RoHS directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition
- Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

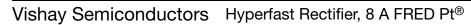
These devices are intended for use in PFC boost stage in the ac-to-dc section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Peak repetitive reverse voltage	V_{RRM}		600	V	
Average rectified forward current FULL-PAK	I _{F(AV)}	T _C = 129 °C	8		
		T _C = 71 °C	0	Α	
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	77	A	
Peak repetitive forward current	I _{FM}		16		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	=	
Forward voltage V _F	I _F = 8 A	-	2.5	3.2	V	
	I _F = 8 A, T _J = 150 °C	-	1.6	2.0		
Be and below a soul		$V_R = V_R$ rated	-	0.3	40	
Reverse leakage current I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$ - 30		30	400	μΑ	
Junction capacitance	C _T	V _R = 600 V	-	6	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH

Document Number: 93171 Revision: 18-Aug-10





DYNAMIC RECOVERY		, ,		•	· ·	MAY	LINUTO
PARAMETER	SYMBOL	TEST C	ONDITIONS	MIN.	TYP.	MAX.	UNITS
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		ı	13	18	_
		$I_F = 8.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		=	14	23	
		T _J = 25 °C	I _F = 8 A	-	16	-	ns
	t _{rr}	T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	35	-	
			$I_F = 8 A$ $dI_F/dt = 600 A/\mu s$ $V_R = 390 V$	-	25	-	
Peak recovery current I _{RRN}		T _J = 25 °C	$I_F = 8 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$	-	2.3	-	Α
	loov	I _{RRM} T _J = 125 °C	$V_R = 390 \text{ V}$	-	3.8	-	
	чкм		$I_F = 8 \text{ A}$ $dI_F/dt = 600 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	10	-	
Reverse recovery charge		T _J = 25 °C	I _F = 8 A	-	16	-	nC
	Q _{rr}	T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	62	-	
	∀ rr		$I_F = 8 \text{ A}$ $dI_F/dt = 600 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	131	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance,	D		-	2	2.4	
junction to case FULL-PAK	R_{thJC}		-	5	5.5	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Woight			-	2	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)
Marking davise		Case style TO-220	8E2TX06			
Marking device		Case style TO-220 FULL-PAK	8E2TX06FP			





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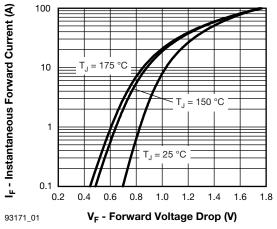


Fig. 1 - Typical Forward Voltage Drop Characteristics

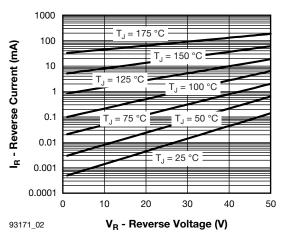


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

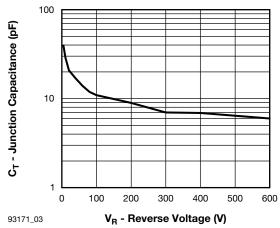


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

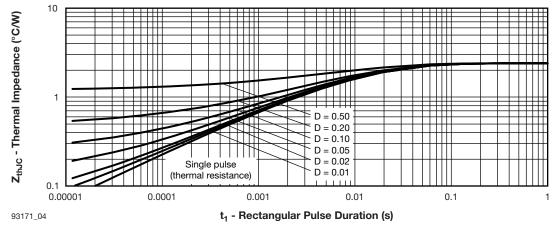


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (TO-220)

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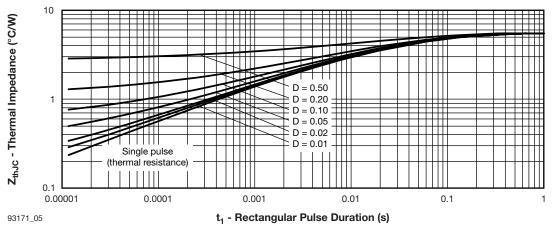


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

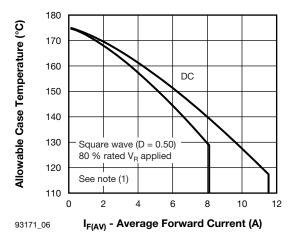


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current (TO-220)

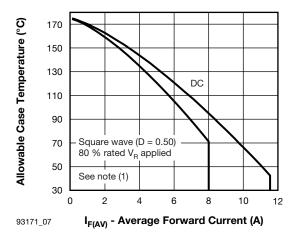


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

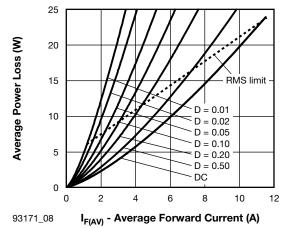


Fig. 8 - Forward Power Loss Characteristics

Note

 $^{(1)} \ \ Formula \ used: T_C = T_J - (Pd + Pd_{REV}) \ x \ R_{thJC}; Pd = Forward \ power \ loss = I_{F(AV)} \ x \ V_{FM} \ at \ (I_{F(AV)}/D) \ (see \ fig. \ 6); \\ Pd_{REV} = Inverse \ power \ loss = V_{R1} \ x \ I_R \ (1 - D); \ I_R \ at \ V_{R1} = Rated \ V_R$



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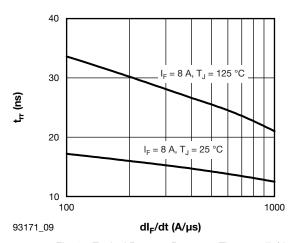


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

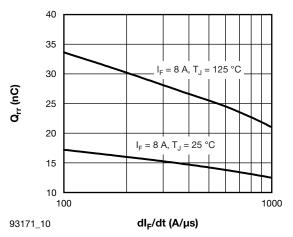


Fig. 10 - Typical Stored Charge vs. dl_F/dt

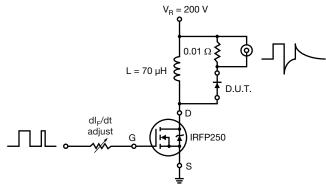
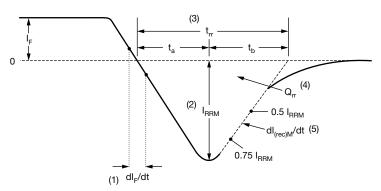


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

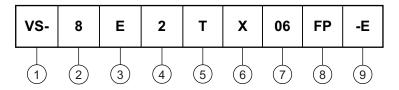
Fig. 12 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 8 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product suffix

2 - Current rating (8 = 8 A)

3 - Circuit configuration:

E = Single diode

4 - 2 = True 2 pin package

5 - T = TO-220

6 - X = Hyperfast recovery time

7 - Voltage code (06 = 600 V)

8 - • None = TO-220

• FP = FULL-PAK

9 - Environmental digit:

• -E = RoHS compliant and terminations lead (Pb)-free

• -M = Halogen-free, RoHS compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-8E2TX06-E	50	1000	Antistatic plastic tubes		
VS-8E2TX06-M	50	1000	Antistatic plastic tubes		
VS-8E2TX06FP-E	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS				
Dimensions	TO-220AC	www.vishay.com/doc?95259		
Dimensions	TO-220 FULL-PAK	www.vishay.com/doc?95260		
TO-220AC		www.vishay.com/doc?95391		
Part marking information	TO-220 FULL-PAK	www.vishay.com/doc?95392		
Packaging information		www.vishay.com/doc?95388		

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Document Number: 91000 www.vishay.com
Revision: 11-Mar-11 1